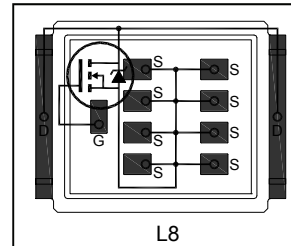


- Advanced Process Technology
- Optimized for Automotive Motor Drive, DC-DC and other Heavy Load Applications
- Exceptionally Small Footprint and Low Profile
- High Power Density
- Low Parasitic Parameters
- Dual Sided Cooling
- 175°C Operating Temperature
- Repetitive Avalanche Allowed up to Tjmax
- Lead Free, RoHS Compliant and Halogen Free
- Automotive Qualified \*

$V_{(BR)DSS}$	<b>60V</b>
$R_{DS(on)}$ <b>typ.</b>	<b>1.1mΩ</b>
<b>max.</b>	<b>1.5mΩ</b>
$I_D$ (Silicon Limited)	<b>345A</b>
$Q_g$	<b>183nC</b>



Applicable DirectFET™ Outline and Substrate Outline ①

SB	SC		M2	M4		L4	L6	<b>L8</b>	
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**Description**

The AUIRF7749L2 combines the latest Automotive HEXFET® Power MOSFET Silicon technology with the advanced DirectFET™ packaging technology to achieve exceptional performance in a package that has the footprint of a D-Pak (TO-252AA) and only 0.7mm profile. The DirectFET™ package is compatible with existing layout geometries used in power applications, PCB assembly equipment and vapor phase, infra-red or convection soldering techniques, when application note AN-1035 is followed regarding the manufacturing methods and processes. The DirectFET™ package allows dual sided cooling to maximize thermal transfer in automotive power systems.

This HEXFET® Power MOSFET is designed for applications where efficiency and power density are of value. The advanced DirectFET™ packaging platform coupled with the latest silicon technology allows the AUIRF7749L2 to offer substantial system level savings and performance improvement specifically in motor drive, DC-DC and other heavy load applications on ICE, HEV and EV platforms. This MOSFET utilizes the latest processing techniques to achieve ultra low on-resistance per silicon area. Additional features of this MOSFET are 175°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for high current automotive applications.

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRF7749L2	DirectFET™ Large Can	Tape and Reel	4000	AUIRF7749L2TR

**Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	60	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ④	345	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ④	243	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ③	36	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Package limit) ④	375	
$I_{DM}$	Pulsed Drain Current ⑤	1380	
$P_D @ T_C = 25^\circ C$	Power Dissipation ④	341	W
$P_D @ T_A = 25^\circ C$	Power Dissipation ③	3.8	
$E_{AS}$	Single Pulse Avalanche Energy (Thermally Limited) ⑥	315	mJ
$E_{AS} (Tested)$	Single Pulse Avalanche Energy ⑥	714	
$I_{AR}$	Avalanche Current ⑤	See Fig. 16, 17, 18a, 18b	A
$E_{AR}$	Repetitive Avalanche Energy ⑤		mJ
$T_P$	Peak Soldering Temperature	270	°C
$T_J$	Operating Junction and	-55 to + 175	
$T_{STG}$	Storage Temperature Range		

HEXFET® is a registered trademark of International Rectifier.

\*Qualification standards can be found at : [www.infineon.com](http://www.infineon.com)

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③	—	40	°C/W
$R_{\theta JA}$	Junction-to-Ambient ⑧	12.5	—	
$R_{\theta JA}$	Junction-to-Ambient ⑨	20	—	
$R_{\theta J-Can}$	Junction-to-Can ④⑩	—	0.44	
$R_{\theta J-PCB}$	Junction-to-PCB Mounted	—	0.5	
	Linear Derating Factor ④	2.3		W/°C

**Static Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

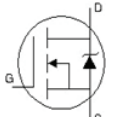
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	56	—	mV/°C	Reference to $25^\circ\text{C}$ , $I_D = 3.0\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.1	1.5	m $\Omega$	$V_{GS} = 10V, I_D = 120A$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-8.8	—	mV/°C	
gfs	Forward Trans conductance	185	—	—	S	$V_{DS} = 10V, I_D = 120A$
$R_G$	Internal Gate Resistance	—	1.5	—	$\Omega$	
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 60V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 60V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

**Dynamic Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge	—	183	275	nC	$V_{DS} = 30V$ $V_{GS} = 10V$ $I_D = 120A$
$Q_{gs1}$	Gate-to-Source Charge	—	39	—		
$Q_{gs2}$	Gate-to-Source Charge	—	19	—		
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	46	—		
$Q_{godr}$	Gate Charge Overdrive	—	79	—		
$Q_{sw}$	Switch Charge ( $Q_{gs2} + Q_{gd}$ )	—	65	—		
$Q_{oss}$	Output Charge	—	119	—	nC	$V_{DS} = 48V, V_{GS} = 0V$
$t_{d(on)}$	Turn-On Delay Time	—	29	—	ns	$V_{DD} = 30V, V_{GS} = 10V$ ⑦ $I_D = 120A$ $R_G = 1.8\Omega$
$t_r$	Rise Time	—	149	—		
$t_{d(off)}$	Turn-Off Delay Time	—	72	—		
$t_f$	Fall Time	—	88	—		
$C_{iss}$	Input Capacitance	—	10655	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	1627	—		$V_{DS} = 25V$
$C_{riss}$	Reverse Transfer Capacitance	—	680	—		$f = 1.0\text{MHz}$
$C_{oss\text{ eff.}}$	Effective Output Capacitance	—	1959	—		$V_{GS} = 0V, V_{DS} = 0V\text{ to }48V$

Notes ① through ⑩ are on page 11

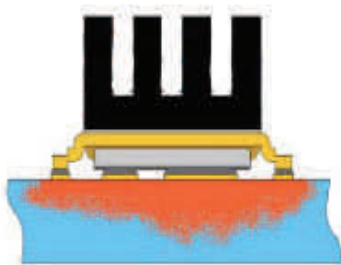
**Diode Characteristics**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	345	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ⑤	—	—	1380		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}$ , $I_S = 120\text{A}$ , $V_{GS} = 0\text{V}$ ⑦
$t_{rr}$	Reverse Recovery Time	—	42	—	ns	$I_F = 120\text{A}$ , $V_{DD} = 30\text{V}$
$Q_{rr}$	Reverse Recovery Charge	—	54	—	nC	$di/dt = 100\text{A}/\mu\text{s}$ ⑧

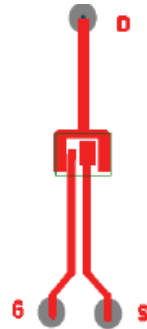
Notes ① through ⑩ are on page 11



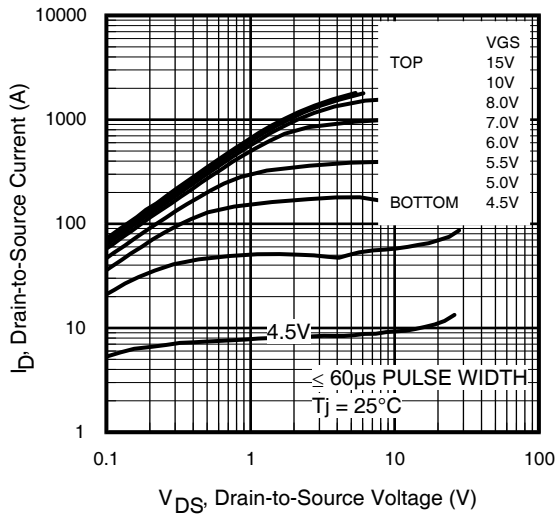
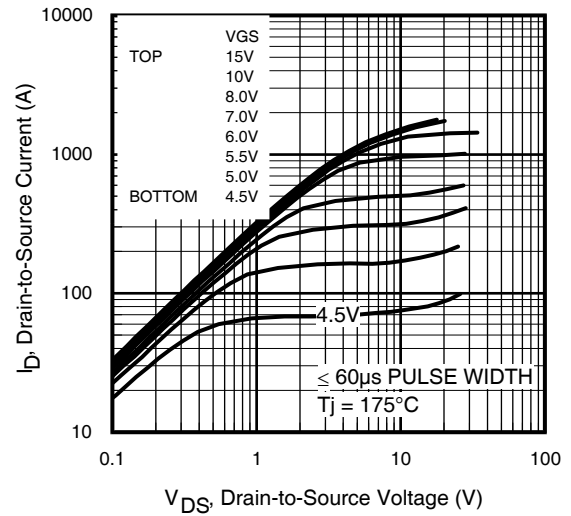
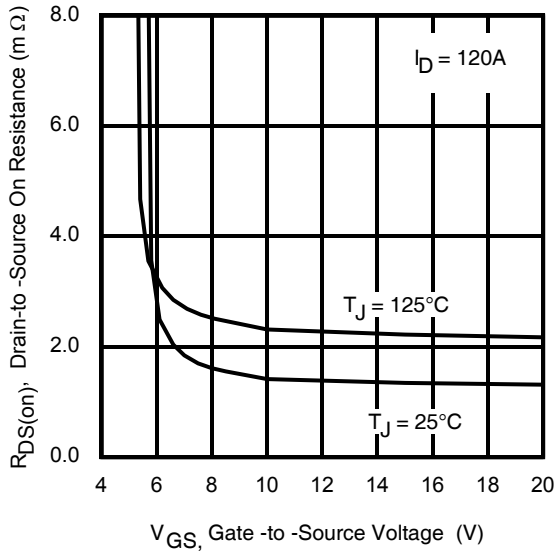
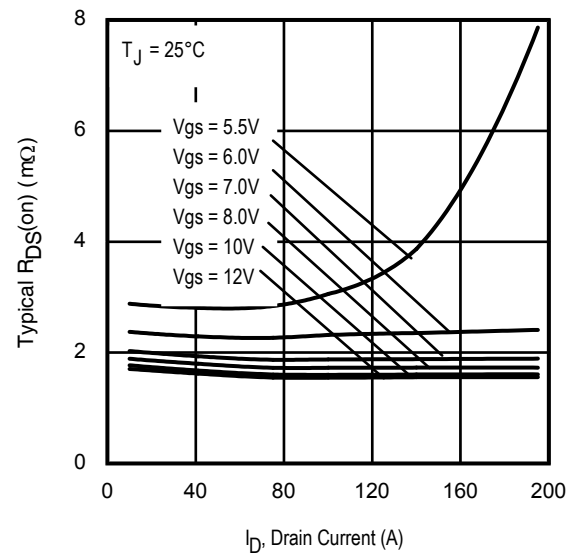
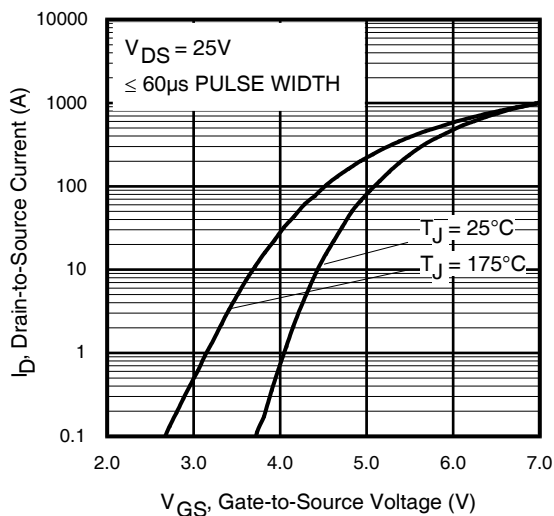
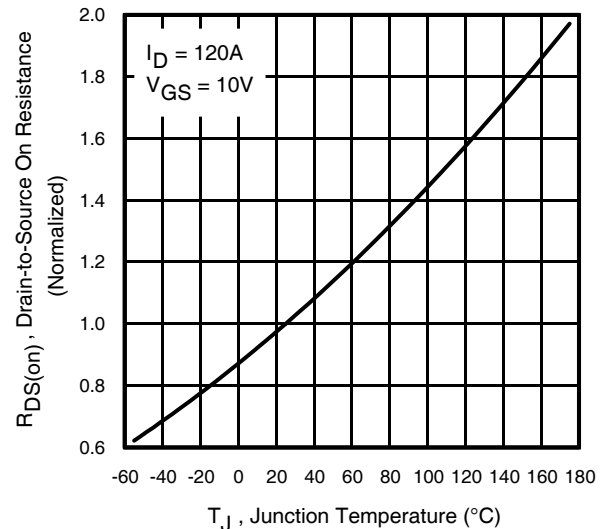
③ Surface mounted on 1 in. square Cu board (still air).

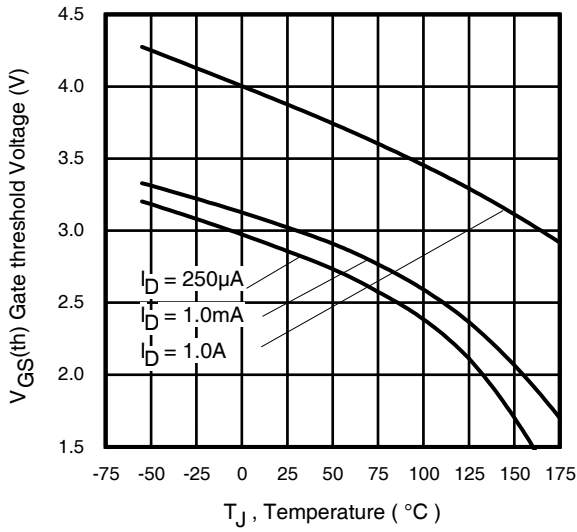
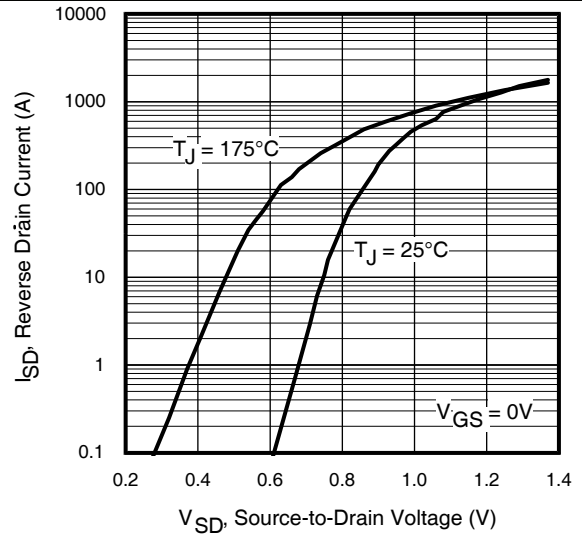
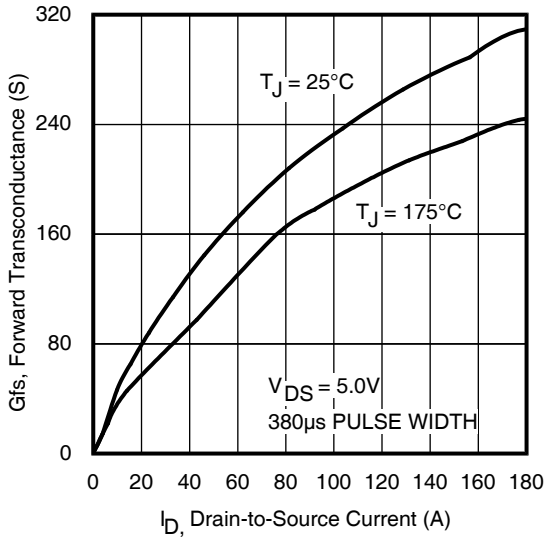
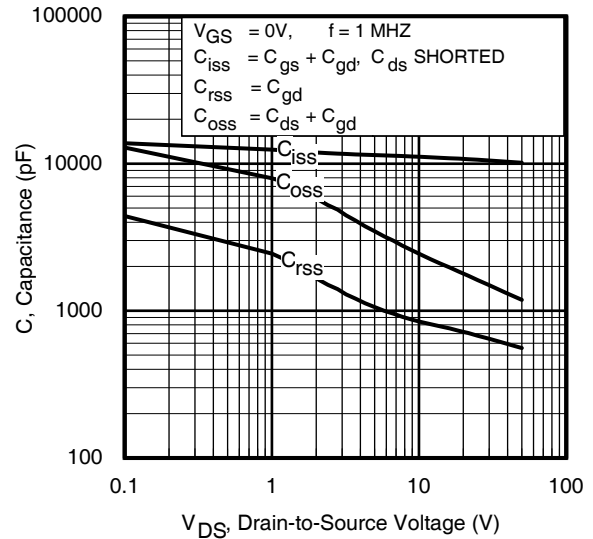
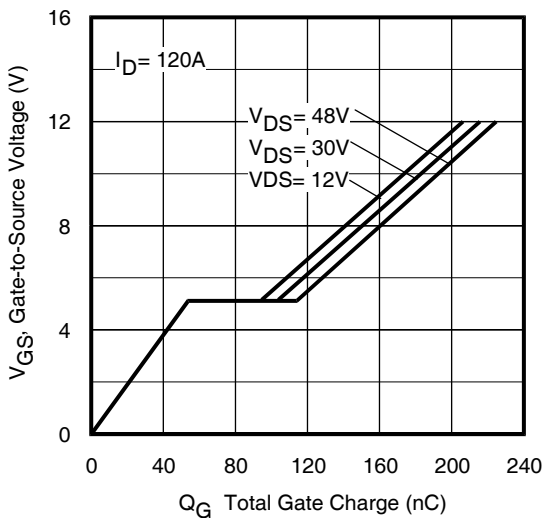
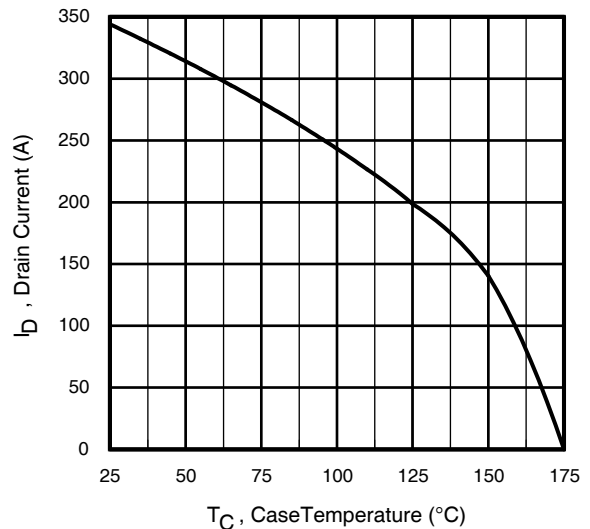


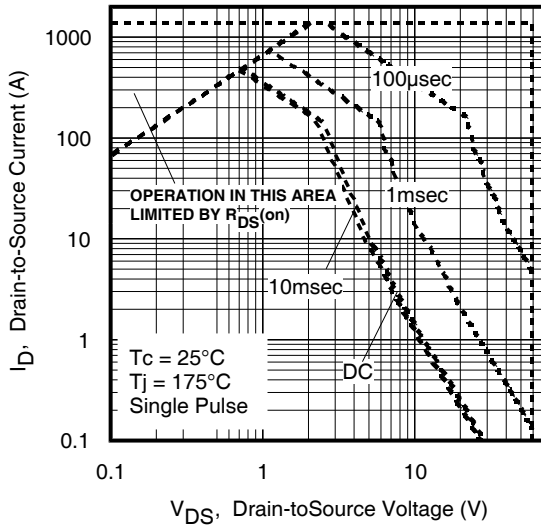
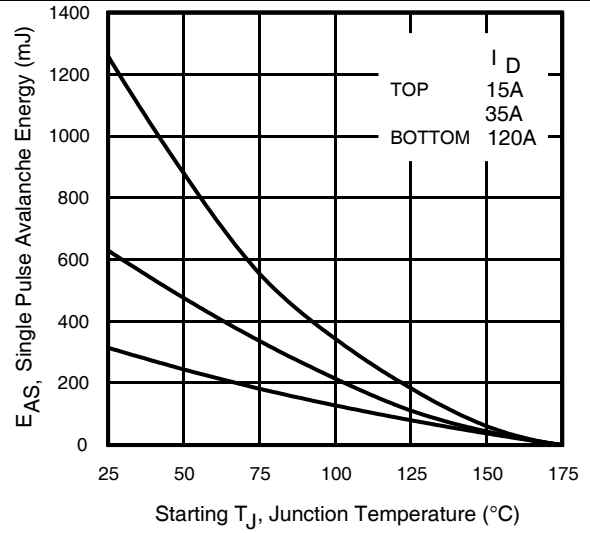
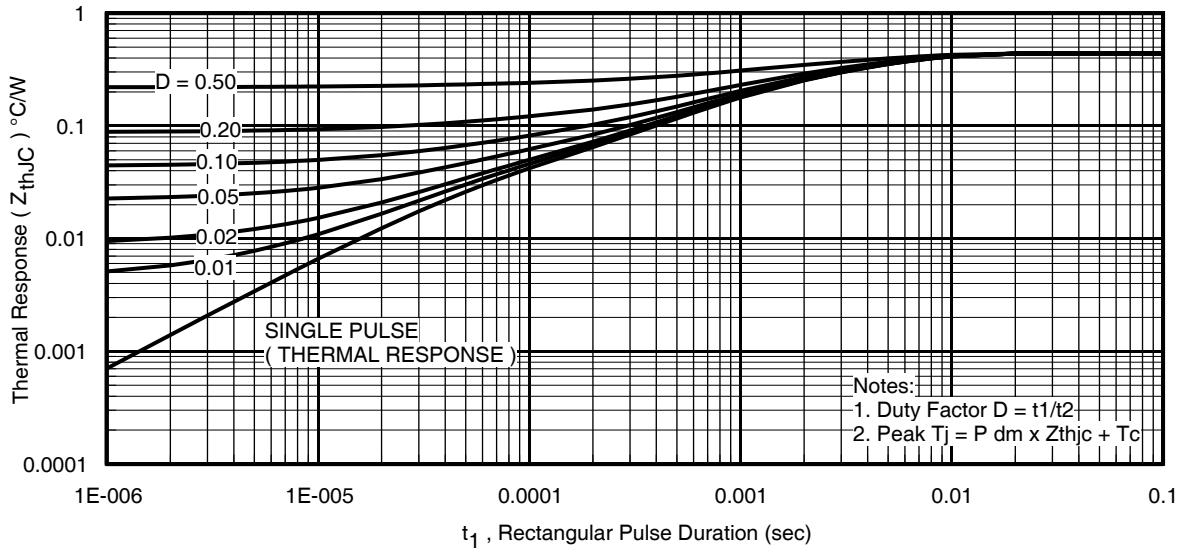
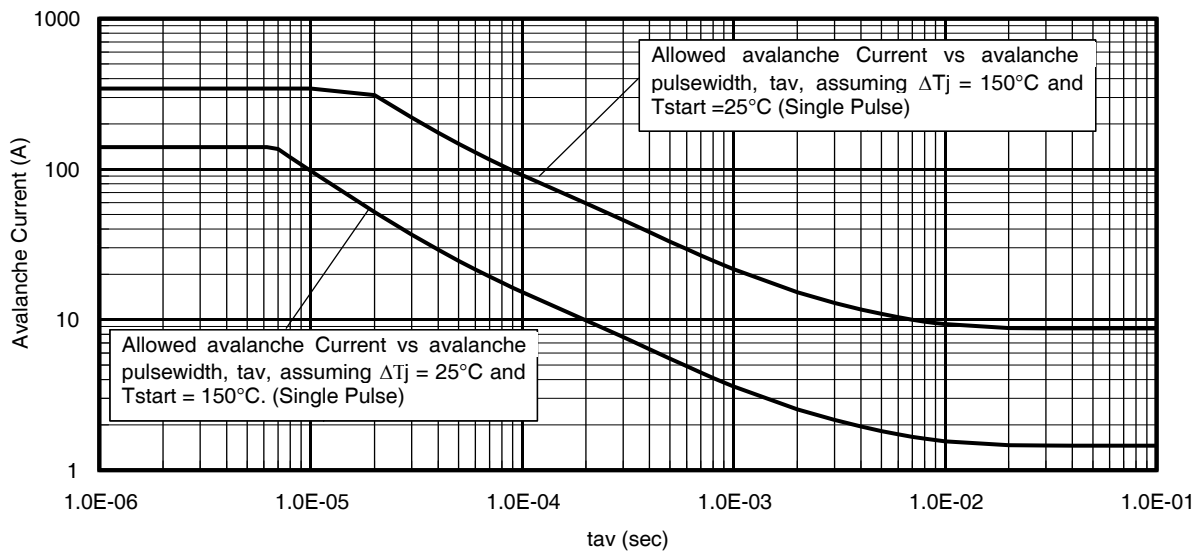
⑨ Mounted to a PCB with small clip heatsink (still air)

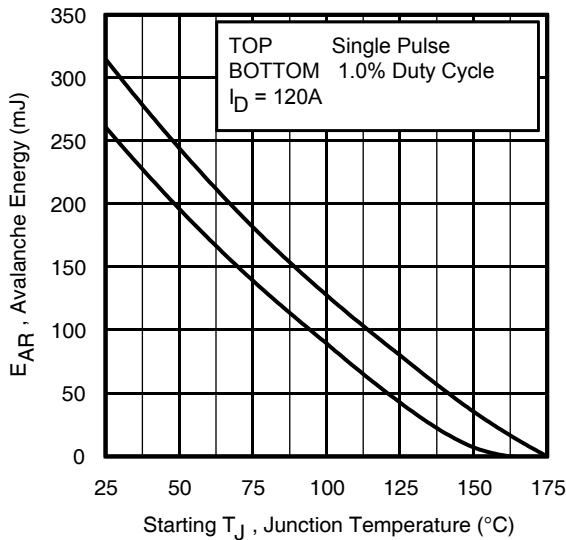


⑩ Mounted on minimum footprint full size board with metalized back and with small clip heatsink (still air).


**Fig. 1** Typical Output Characteristics

**Fig. 2** Typical Output Characteristics

**Fig. 3** Typical On-Resistance vs. Gate Voltage

**Fig. 4** Typical On-Resistance vs. Drain Current

**Fig 5.** Transfer Characteristics

**Fig 6.** Normalized On-Resistance vs. Temperature


**Fig. 7** Typical Threshold Voltage vs. Junction Temperature

**Fig. 8.** Typical Source-Drain Diode Forward Voltage

**Fig 9.** Typical Forward Trans conductance vs. Drain Current

**Fig 10.** Typical Capacitance vs. Drain-to-Source Voltage

**Fig 11.** Typical Gate Charge vs. Gate-to-Source Voltage

**Fig 12.** Maximum Drain Current vs. Case Temperature


**Fig 13. Maximum Safe Operating Area**

**Fig 14. Maximum Avalanche Energy vs. Temperature**

**Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**Fig 16. Typical Avalanche Current vs. Pulse Width**

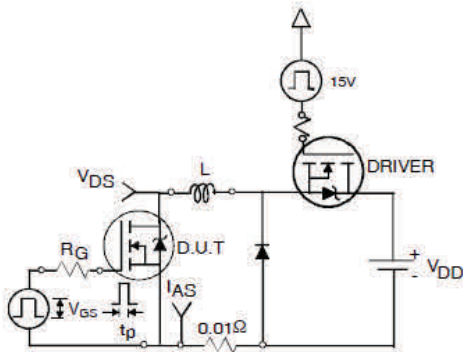
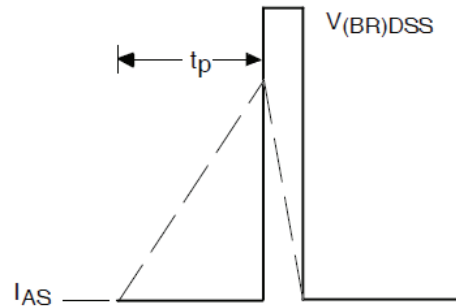
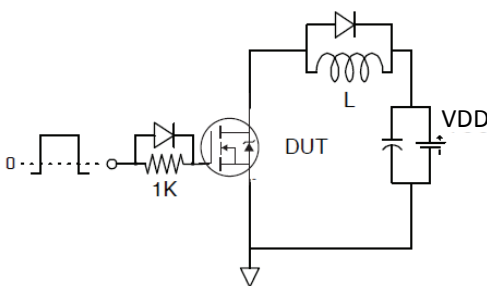
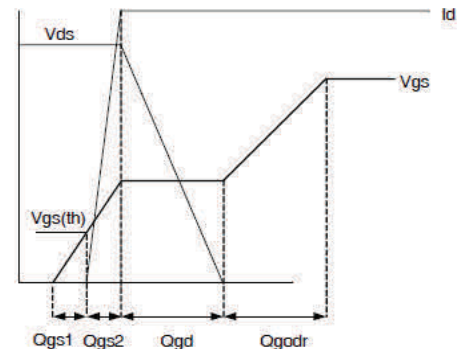
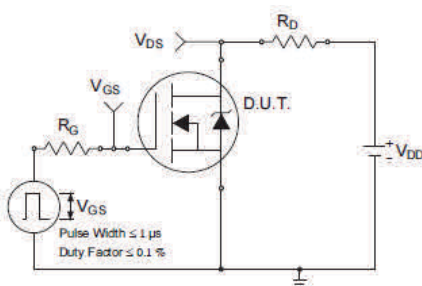
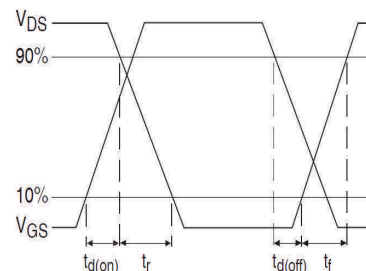

**Fig 17. Maximum Avalanche Energy vs. Temperature**
**Notes on Repetitive Avalanche Curves , Figures 16, 17:**
**(For further info, see AN-1035 at [www.infineon.com](http://www.infineon.com))**

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 18a, 18b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 16, 17).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 15)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

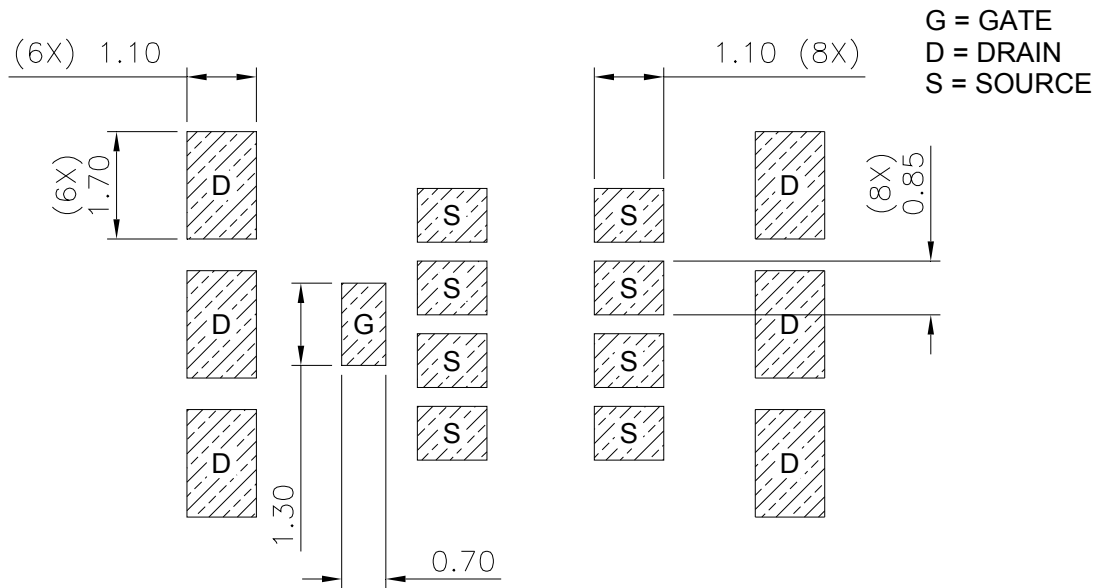
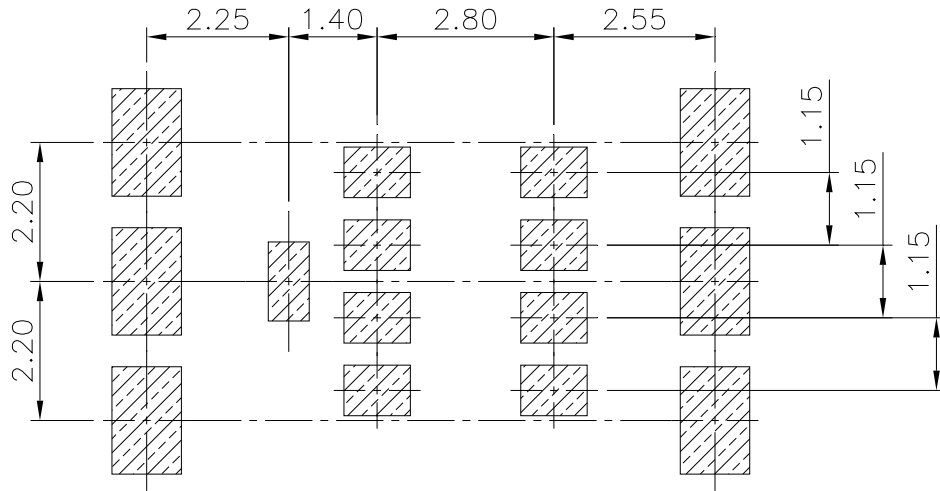
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$


**Fig 18a. Unclamped Inductive Test Circuit**

**Fig 18b. Unclamped Inductive Waveforms**

**Fig 19a. Gate Charge Test Circuit**

**Fig 19b. Gate Charge Waveform**

**Fig 20a. Switching Time Test Circuit**

**Fig 20b. Switching Time Waveforms**

**DirectFET™ Board Footprint, L8 Outline  
(Large Size Can, 8-Source Pads)**

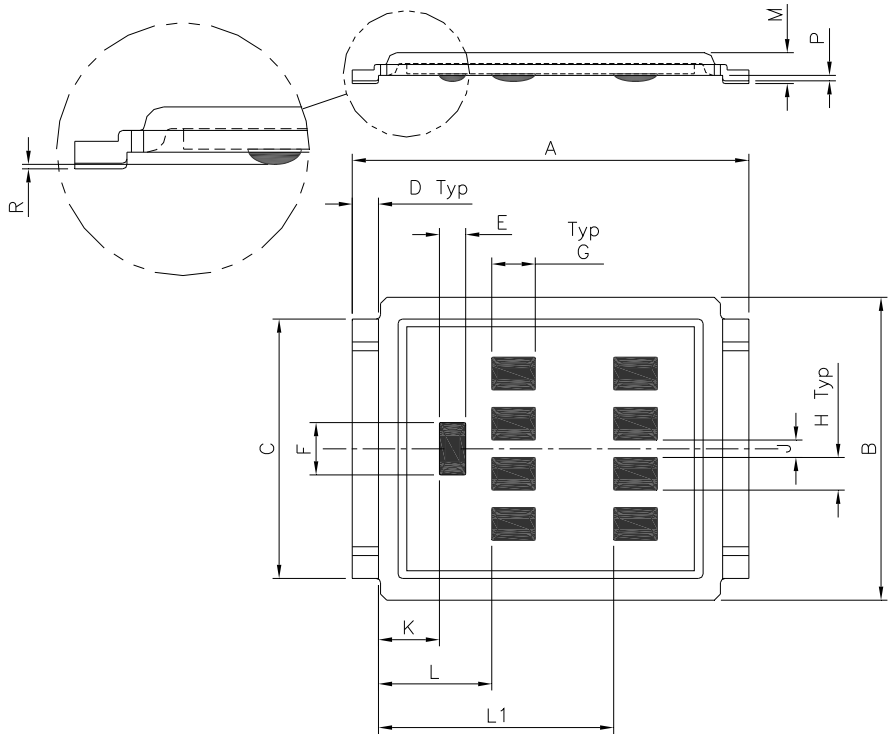
Please see DirectFET™ application note [AN-1035](#) for all details regarding the assembly of DirectFET™. This includes all recommendations for stencil and substrate designs.





**DirectFET™ Outline Dimension, L8 Outline  
(Large Size Can, 8-Source Pads)**

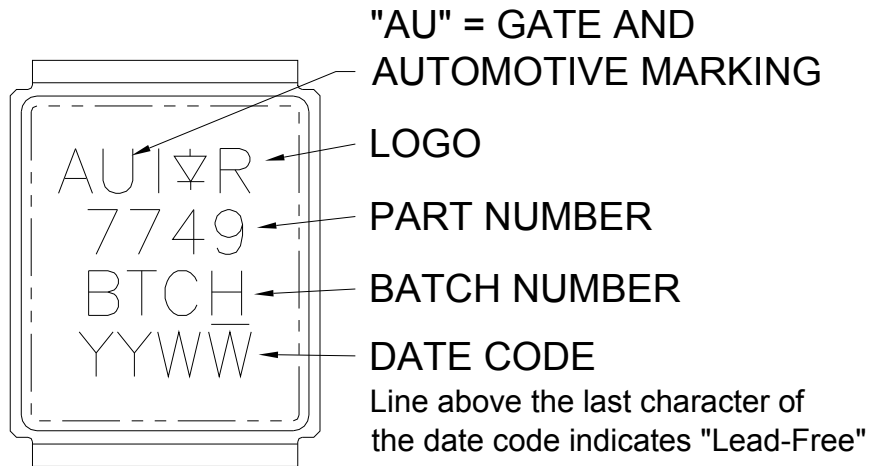
Please see DirectFET™ application note [AN-1035](#) for all details regarding the assembly of DirectFET™. This includes all recommendations for stencil and substrate designs.



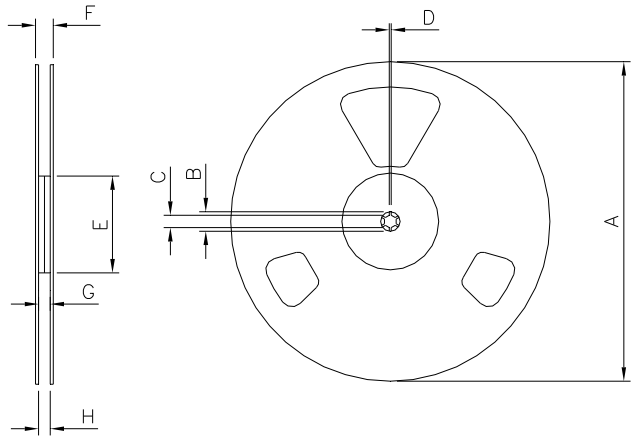
CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	9.05	9.15	0.356	0.360
B	6.85	7.10	0.270	0.280
C	5.90	6.00	0.232	0.236
D	0.55	0.65	0.022	0.026
E	0.58	0.62	0.023	0.024
F	1.18	1.22	0.046	0.048
G	0.98	1.02	0.039	0.040
H	0.73	0.77	0.029	0.030
J	0.38	0.42	0.015	0.017
K	1.35	1.45	0.053	0.057
L	2.55	2.65	0.100	0.104
L1	5.35	5.45	0.211	0.215
M	0.68	0.74	0.027	0.029
P	0.09	0.17	0.003	0.007
R	0.02	0.08	0.001	0.003

Dimensions are shown in millimeters (inches)

**DirectFET™ Part Marking**



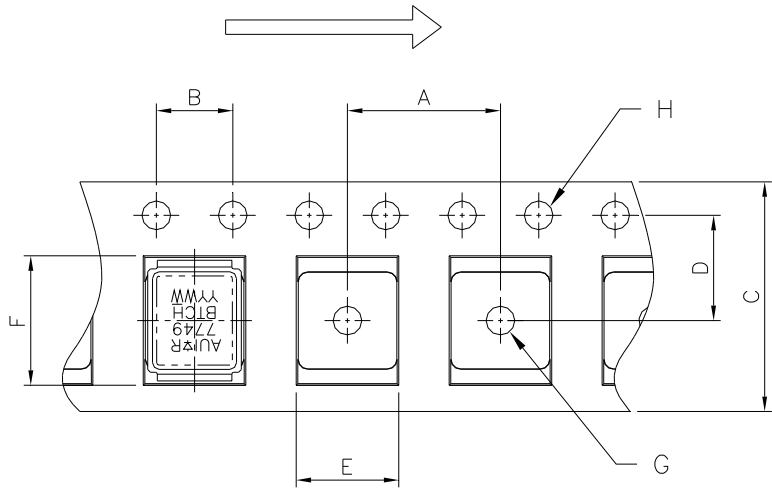
**DirectFET™ Tape & Reel Dimension (Showing component orientation)**



NOTE: Controlling dimensions in mm  
Std reel quantity is 4000 parts. (ordered as AUIRF7749L2TR).

REEL DIMENSIONS				
STANDARD OPTION (QTY 4000)				
CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	330.00	N.C	12.992	N.C
B	20.20	N.C	0.795	N.C
C	12.80	13.20	0.504	0.520
D	1.50	N.C	0.059	N.C
E	99.00	100.00	3.900	3.940
F	N.C	22.40	N.C	0.880
G	16.40	18.40	0.650	0.720
H	15.90	19.40	0.630	0.760

**LOADED TAPE FEED DIRECTION**



NOTE: CONTROLLING DIMENSIONS IN MM

CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	11.90	12.10	4.69	0.476
B	3.90	4.10	0.154	0.161
C	15.90	16.30	0.623	0.642
D	7.40	7.60	0.291	0.299
E	7.20	7.40	0.283	0.291
F	9.90	10.10	0.390	0.398
G	1.50	N.C	0.059	N.C
H	1.50	1.60	0.059	0.063

**Qualification Information**

<b>Qualification Level</b>		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		DirectFET2 L-CAN	MSL1
<b>ESD</b>	Machine Model	Class M4 (+/- 800V) <sup>†</sup>	
		AEC-Q101-002	
	Human Body Model	Class H2 (+/- 4000V) <sup>†</sup>	
		AEC-Q101-001	
<b>RoHS Compliant</b>		Yes	

† Highest passing voltage.

- ① Click on this section to link to the appropriate technical paper.
- ② Click on this section to link to the Direct FET™ Website.
- ③ Surface mounted on 1 in. square Cu board, steady state.
- ④  $T_C$  measured with thermocouple mounted to top (Drain) of part.
- ⑤ Repetitive rating; pulse width limited by max. junction temperature.

- ⑥ Limited by  $T_{Jmax}$ , Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.044\text{mH}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 120\text{A}$ .
- ⑦ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑧ Used double sided cooling, mounting pad with large heat sink.
- ⑨ Mounted on minimum footprint full size board with metalized back and with small clip heat sink.
- ⑩  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .

**Revision History**

Date	Comments
10/11/2016	<ul style="list-style-type: none"> <li>• Changed datasheet with “Infineon” logo –all pages.</li> <li>• Corrected typo on Absolute Maximum Ratings table –from “V<sub>GS</sub>” to “V<sub>DS</sub>” on page 1.</li> <li>• Added disclaimer on last page.</li> </ul>

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